NSN 5962-01-368-5362

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Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Eots e/i fscm 76301
Features Provided:
Programmable
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
22 input
Case Outline Source And Designator:
D-9 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital memory, bipolar programmable logic
Voltage Rating And Type Per Characteristic:
-0.5 volts applied and 7.0 volts applied and 4.5 volts positive power supply span and 5.5 volts positive power supply span
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883
standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit

Shelf Life:

Specification Data:

Specification Or Standard: 03 type and I case and a finish

67268-5962-86053 government standard

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Demilitarization:

Yes - demil/mli

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